AMENDMENTS TO THE CLAIMS:

1. (Currently amended) An electrode for a p-type Group III nitride compound semiconductor, comprising:

a film including a ~~at least containing~~ polycrystalline metal.

2. (Currently amended) An electrode for a p-type Group III nitride compound semiconductor according to claim 1, wherein said polycrystalline metal comprises ~~has such~~ a fiber structure in which ~~that~~ crystal planes of crystal grains are oriented.

3. (Currently amended) An electrode for a p-type Group III nitride compound semiconductor according to claim 1, wherein said polycrystalline metal comprises ~~has~~ large crystal grains.

4-6. (Canceled).

7. (New) The electrode according to claim 1, wherein the polycrystalline metal comprises a fiber structure in which a crystal grain boundary density decreases such that a quantity of defects in the metal/semiconductor boundary decreases.

8. (New) The electrode according to claim 2, wherein a percentage of oriented crystal grains occupying said fiber structure is increased to provide an increase of an orientation force of the metal film.

9. (New) The electrode according to claim 2, wherein said fiber structure comprises a predetermined percentage of oriented crystal grains to provide a predetermined orientation force of the metal film.

10. (New) The electrode according to claim 1, wherein the polycrystalline metal comprises a fiber structure including oriented crystal faces including closed packed planes.

11. (New) An electrode for a p-type Group III nitride compound semiconductor, the electrode comprising:

a polycrystalline metal film disposed on said p-type Group III nitride compound semiconductor to form a metal/semiconductor boundary,

wherein said polycrystalline metal film comprises a fiber structure in which a crystal grain boundary density decreases such that a quantity of defects in the metal/semiconductor boundary decreases.

12. (New) The electrode according to claim 11, wherein said fiber structure of said polycrystalline metal film comprises oriented crystal planes of crystal grains.

13. (New) The electrode according to claim 11, wherein said polycrystalline metal comprises crystal grains of a predetermined large size.

14. (New) The electrode according to claim 12, wherein a percentage of oriented crystal grains occupying said fiber structure is increased to provide an increase of an orientation force of the metal film.

15. (New) The electrode according to claim 11, wherein the polycrystalline metal comprises a fiber structure including oriented crystal faces including closed packed planes.

16. (New) The electrode according to claim 11, wherein said p-type Group III nitride compound semiconductor comprises one of GaN, AlGaN, and GaInN.

17. (New) The electrode according to claim 11, wherein said polycrystalline metal comprises one of platinum (Pt), nickel (Ni, palladium (Pd), chromium (Cr), and iron (Fe).

18. (New) The electrode according to claim 11, wherein a degree of said crystal grains of said predetermined large size is no less than a thickness of said polycrystalline metal film.

19. (New) A p-type Group III nitride compound semiconductor light-emitting device, comprising:

an electrode including a polycrystalline metal film disposed on a p-type Group III nitride compound semiconductor layer of said light-emitting device to form a metal/semiconductor boundary,

wherein said polycrystalline metal film comprises a fiber structure in which a crystal grain boundary density decreases such that a quantity of defects in the metal/semiconductor boundary decreases.

20. (New) The device according to claim 19, wherein said fiber structure of said polycrystalline metal film comprises oriented crystal planes of crystal grains.

21. (New) The device according to claim 19, wherein said polycrystalline metal comprises crystal grains of a predetermined large size.